Docket No. 20661-801D1

IN THE CLAIMS

Please amend the claims as follows:

1.(Twice Amended) A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of and on a layer, wherein said polysilicon resistor is formed using a doping wherein said doping has a concentration of from ~$6x10^{19}$ cm^{-3} to ~[3.75] $1x10^{20}$ cm^{-3} and wherein said polycrystalline silicon resistor has at least a first and second order temperature coefficient wherein the sign of said first and second order temperature coefficients are opposite each other; and

wherein said resistor resistance is electronically trimmed.

2.(Twice Amended) A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of on a layer, wherein said polysilicon resistor is formed using a doping wherein said doping has a concentration of less than ~$3.75x10^{20}$ cm^{-3} and wherein said polycrystalline silicon resistor has at least a first and second order temperature coefficient, wherein the sign of said first and second order temperature coefficients are opposite each other; and

wherein said resistor resistance is electronically trimmed.

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11.(Twice amended) A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of on a layer, wherein said polysilicon resistor is formed using a doping wherein said doping has a concentration of greater than ~$6x10^{19}$ cm^{-3} and wherein said polycrystalline silicon resistor has at least a first and second order temperature coefficient, wherein the sign of said first and second order temperature coefficients are opposite each other; and

wherein said resistor resistance is electronically trimmed.

12.(Twice amended) A resistor having a resistance that can be adjusted by current being passed there through and which is formed as part of a semiconductor device comprising:

a polycrystalline silicon resistor formed of on a layer, wherein said polysilicon resistor is formed using a late implant doping technique and wherein said polycrystalline silicon resistor has at least a first and second order temperature coefficient, wherein the sign of said first and second order temperature coefficients are opposite each other; and

wherein said resistor resistance is electronically trimmed.